

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-17. (Cancelled)

18. (New) Method for recording data by means of an array of micro-tips arranged in a plane facing a memory support, comprising a stack of thin layers with at least one deformable memory layer, method comprising data recording by selective actuation of the micro-tips, wherein, the micro-tips being fixed directly onto one and the same support substrate, the method comprises bringing the array of micro-tips and the memory support into contact with a predetermined pressure, before selective actuation of micro-tips for data recording, said pressure enabling the dispersion of the dimensions of the micro-tips of the array of micro-tips to be absorbed by the deformable memory layer.

19. (New) Method according to claim 18, wherein data recording is of electric type.

20. (New) Method according to claim 18, wherein data recording is of thermal type.

21. (New) Method according to claim 18, wherein data recording is performed by applying a mechanical pressure greater than the pressure of bringing into contact.

22. (New) Recording device for implementation of the method according to claim 18, comprising an array of micro-tips arranged in a plane facing a memory support, comprising a stack of thin layers with at least one deformable memory layer, means for absorbing the dispersion of the dimensions of the micro-tips of the array and means for recording by selective actuation of the micro-tips, wherein the deformable memory layer constitutes said means for absorbing when the memory support and the array of micro-tips are brought into contact, at said predetermined pressure, the micro-tips, having an apex of nanometric dimension, being fixed directly onto one and the same support substrate.

23. (New) Device according to claim 22, wherein the memory layer is deposited on a flexible layer deposited on the substrate.
24. (New) Device according to claim 23, wherein the flexible layer is made of polymer.
25. (New) Device according to claim 24, wherein the flexible layer is made of photoresist.
26. (New) Device according to claim 23, wherein the flexible layer is a glue of controlled hardness.
27. (New) Device according to claim 23, wherein the flexible layer is made of elastomer silicone.
28. (New) Device according to claim 23, wherein the flexible layer has a thickness of about a few micrometers.
29. (New) Device according to claim 23, wherein the flexible layer is conducting.
30. (New) Device according to claim 23, comprising an additional conducting layer between the memory layer and the flexible layer.
31. (New) Device according to claim 22, wherein the memory layer has a thickness of less than one micrometer.
32. (New) Device according to claim 22, comprising an interface layer with the micro-tips, covering the memory layer.
33. (New) Device according to claim 22, wherein the substrate is made of silicon.
34. (New) Device according to claim 22, wherein the substrate is made of plastic material with a thickness of less than one millimeter.